AMENDMENTS TO THE CLAIMS

- 1. (currently amended) An NROM memory transistor comprising:
 - a substrate having a plurality of source/drain regions, the source/drain regions having a different conductivity type than the remainder of the substrate;
 - a nanolaminate, high permittivity (high-k), oxidized metal gate dielectric formed by an oxidation of metal overlying the substrate, the gate dielectric having a dielectric constant greater than a dielectric constant of silicon dioxide; and a control gate formed on top of the gate dielectric.
- 2. (original) The transistor of claim 1 wherein the gate dielectric is a composite oxide high-k dielectric oxide nanolaminate gate insulator wherein the high-k dielectric is a charge trapping layer formed by low temperature oxidation of metal.
- 3. (canceled)
- 4. (original) The transistor of claim 1 wherein the transistor is used in either a NOR-type flash memory structure or a NAND-type flash memory structure.
- 5. (original) The transistor of claim 2 wherein the charge trapping layer is comprised of a material that has a lower conduction band edge than silicon nitride.
- 6. (original) The transistor of claim 2 wherein the gate dielectric has a larger energy barrier between the high-k dielectric and the oxide insulator than silicon dioxide.
- 7. (original) The transistor of claim 1 wherein the gate dielectric is comprised of one of the following structures: oxide oxidized Hf oxide, oxide oxidized Zr oxide, or oxide oxidized Al oxide.
- 8-37 (canceled)

RESPONSE TO NON-FINAL OFFICE ACTION

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Serial No. 10/808,059 Attorney Docket No. 400.285US01
Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC FORMED BY THE

LOW TEMPERATURE OXIDIZATION OF METALS

48. (canceled)